

MOSFETs Silicon N-channel MOS (U-MOSIX-H)

TPN3R704PL

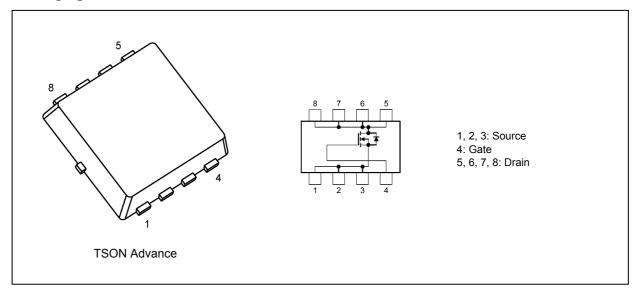
1. Applications

- · High-Efficiency DC-DC Converters
- Switching Voltage Regulators
- · Motor Drivers

2. Features

- (1) High-speed switching
- (2) Small gate charge: $Q_{SW} = 8.1 \text{ nC (typ.)}$
- (3) Small output charge: $Q_{oss} = 20.2 \text{ nC (typ.)}$
- (4) Low drain-source on-resistance: $R_{DS(ON)} = 3.0 \text{ m}\Omega$ (typ.) ($V_{GS} = 10 \text{ V}$)
- (5) Low leakage current: $I_{DSS} = 10 \mu A \text{ (max) (V}_{DS} = 40 \text{ V)}$
- (6) Enhancement mode: $V_{th} = 1.4$ to 2.4 V ($V_{DS} = 10$ V, $I_D = 0.2$ mA)

3. Packaging and Internal Circuit





4. Absolute Maximum Ratings (Note) (Ta = 25 °C unless otherwise specified)

| Characteristics | | | Symbol | Rating | Unit |
|--------------------------------|-------------------------|--------------------|-----------------|------------|------|
| Drain-source voltage | | | V_{DSS} | 40 | V |
| Gate-source voltage | | | V_{GSS} | ±20 | |
| Drain current (DC) | $(T_c = 25 ^{\circ}C)$ | (Note 1), (Note 2) | I_D | 80 | Α |
| Drain current (DC) | (Silicon limit) | (Note 1), (Note 2) | I_{D} | 92 | Α |
| Drain current (pulsed) | (t = 100 μs) | (Note 1) | I_{DP} | 200 | Α |
| Power dissipation | $(T_c = 25 ^{\circ}C)$ | | P_{D} | 86 | W |
| Power dissipation | | (Note 3) | P_{D} | 2.67 | W |
| Power dissipation | | (Note 4) | P_{D} | 0.63 | W |
| Single-pulse avalanche energy | | (Note 5) | E _{AS} | 10 | mJ |
| Single-pulse avalanche current | | (Note 5) | I _{AS} | 80 | Α |
| Channel temperature | | | T _{ch} | 175 | °C |
| Storage temperature | | | T_{stg} | -55 to 175 | °C |

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

5. Thermal Characteristics

| Characteristics | Symbol | Max | Unit | | |
|---------------------------------------|--------------------------|----------|-----------------------|------|------|
| Channel-to-case thermal resistance | (T _c = 25 °C) | | R _{th(ch-c)} | 1.73 | °C/W |
| Channel-to-ambient thermal resistance | (T _a = 25 °C) | (Note 3) | R _{th(ch-a)} | 56 | |
| Channel-to-ambient thermal resistance | (T _a = 25 °C) | (Note 4) | R _{th(ch-a)} | 235 | |

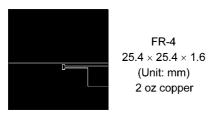
Note 1: Ensure that the channel temperature does not exceed 175 °C.

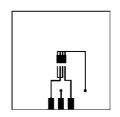
Note 2: Limited by package limit. Silicon chip capability is 92 A. (T_c = 25 °C)

Note 3: Device mounted on a glass-epoxy board (a), Figure 5.1

Note 4: Device mounted on a glass-epoxy board (b), Figure 5.2

Note 5: V_{DD} = 32 V, T_{ch} = 25 °C (initial), L = 1.3 μH , I_{AS} = 80 A





FR-4 25.4 × 25.4 × 1.6 (Unit: mm) 2 oz copper

Fig. 5.1 Device Mounted on a Glass-Epoxy Board (a)

Fig. 5.2 Device Mounted on a Glass-Epoxy Board (b)

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.



6. Electrical Characteristics

6.1. Static Characteristics (T_a = 25 °C unless otherwise specified)

| Characteristics | Symbol | Test Condition | Min | Тур. | Max | Unit |
|--------------------------------|----------------------|---|-----|------|------|------|
| Gate leakage current | I _{GSS} | $V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$ | _ | _ | ±0.1 | μА |
| Drain cut-off current | I _{DSS} | V _{DS} = 40 V, V _{GS} = 0 V | _ | _ | 10 | |
| Drain-source breakdown voltage | V _{(BR)DSS} | I _D = 10 mA, V _{GS} = 0 V | 40 | _ | | ٧ |
| | V _{(BR)DSX} | I _D = 10 mA, V _{GS} = -20 V | 25 | _ | _ | |
| Gate threshold voltage | V_{th} | $V_{DS} = 10 \text{ V}, I_{D} = 0.2 \text{ mA}$ | 1.4 | _ | 2.4 | |
| Drain-source on-resistance | R _{DS(ON)} | V _{GS} = 4.5 V, I _D = 13 A | _ | 4.2 | 6.0 | mΩ |
| | | V _{GS} = 10 V, I _D = 40 A | _ | 3.0 | 3.7 | |

6.2. Dynamic Characteristics (T_a = 25 °C unless otherwise specified)

| Characteristics | Symbol | Test Condition | Min | Тур. | Max | Unit |
|--------------------------------|------------------|--|-----|------|------|------|
| Input capacitance | C _{iss} | V _{DS} = 20 V, V _{GS} = 0 V, f = 1 MHz | _ | 1910 | 2500 | pF |
| Reverse transfer capacitance | C _{rss} | | _ | 41 | 80 | |
| Output capacitance | C _{oss} | | _ | 470 | _ | |
| Gate resistance | r _g | _ | _ | 0.9 | 1.4 | Ω |
| Switching time (rise time) | t _r | See Fig. 6.2.1 | _ | 5.3 | _ | ns |
| Switching time (turn-on time) | t _{on} | | _ | 14.7 | _ | |
| Switching time (fall time) | t _f | | _ | 6.2 | _ | |
| Switching time (turn-off time) | t _{off} | | _ | 24 | _ | |

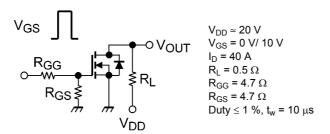


Fig. 6.2.1 Switching Time Test Circuit

6.3. Gate Charge Characteristics (T_a = 25 °C unless otherwise specified)

| Characteristics | Symbol | Test Condition | Min | Тур. | Max | Unit |
|-------------------------------------|------------------|---|-----|------|-----|------|
| Total gate charge (gate-source plus | Q_g | $V_{DD} \approx 20 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 40 \text{ A}$ | _ | 27 | | nC |
| gate-drain) | | $V_{DD} \approx 20 \text{ V}, V_{GS} = 4.5 \text{ V}, I_{D} = 13 \text{ A}$ | _ | 13.3 | | |
| Gate-source charge 1 | Q _{gs1} | $V_{DD} \approx 20 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 40 \text{ A}$ | _ | 7.7 | | |
| Gate-drain charge | Q_{gd} | | _ | 4.2 | _ | |
| Gate switch charge | Q_{SW} | | _ | 8.1 | _ | |
| Output charge | Q _{oss} | V _{DS} = 20 V, V _{GS} = 0 V | _ | 20.2 | _ | |

6.4. Source-Drain Characteristics (T_a = 25 °C unless otherwise specified)

| Characteristics | Symbol | Test Condition | Min | Тур. | Max | Unit |
|---|-------------------------------|---|-----|------|------|------|
| Reverse drain current (pulsed) (Note 6) | I _{DRP} (t = 100 μs) | _ | | | 200 | Α |
| Diode forward voltage | V _{DSF} | I _{DR} = 80 A, V _{GS} = 0 V | | | -1.2 | V |
| Reverse recovery time | t _{rr} | $V_R = 20 \text{ V}, I_{DR} = 20 \text{ A}, V_{GS} = 0$ | _ | 28 | _ | ns |
| Reverse recovery charge | Q _{rr} | V, -dI _{DR} /dt = 100 A/μs | _ | 18.2 | _ | nC |

Note 6: Ensure that the channel temperature does not exceed 175 °C.



7. Marking

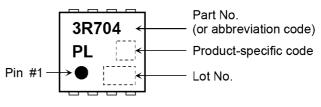


Fig. 7.1 Marking



8. Characteristics Curves (Note)

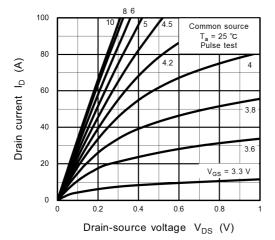


Fig. 8.1 I_D - V_{DS}

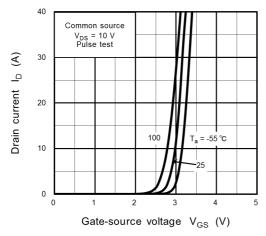


Fig. 8.3 $I_D - V_{GS}$

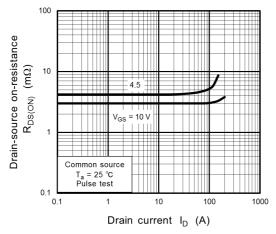


Fig. 8.5 R_{DS(ON)} - I_D

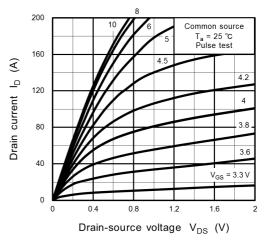


Fig. 8.2 I_D - V_{DS}

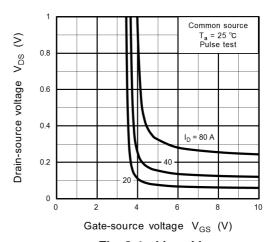


Fig. 8.4 V_{DS} - V_{GS}

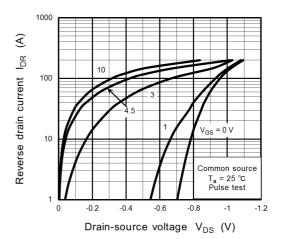


Fig. 8.6 I_{DR} - V_{DS}



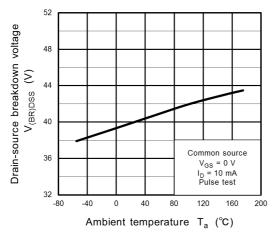


Fig. 8.7 V_{(BR)DSS} - T_a

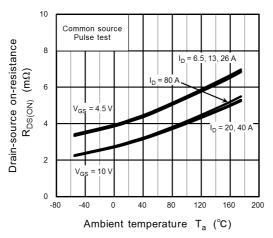


Fig. 8.9 R_{DS(ON)} - T_a

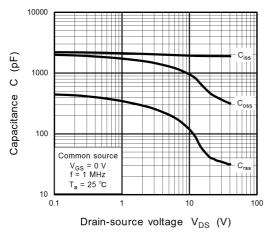


Fig. 8.11 Capacitance - V_{DS}

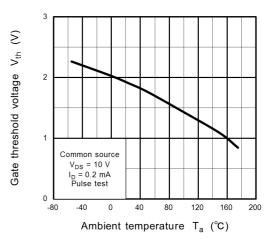


Fig. 8.8 V_{th} - T_a

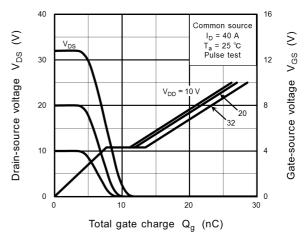


Fig. 8.10 Dynamic Input/Output Characteristics

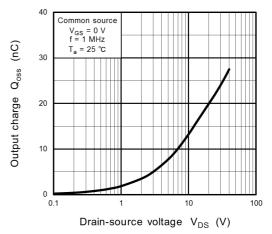


Fig. 8.12 Qoss - VDS



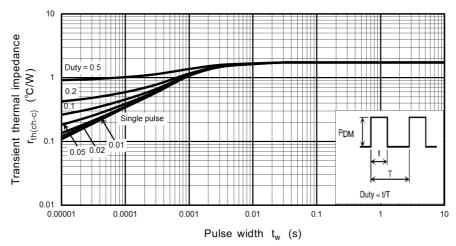


Fig. 8.13 r_{th} - t_w (Guaranteed Maximum)

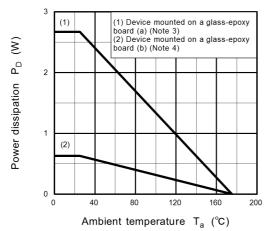


Fig. 8.14 P_D - T_a (Guaranteed Maximum)

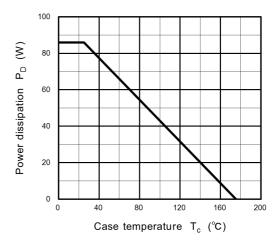


Fig. 8.15 P_D - T_c (Guaranteed Maximum)

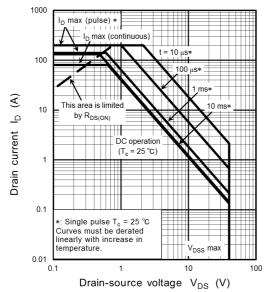


Fig. 8.16 Safe Operating Area (Guaranteed Maximum)

Rev.3.0

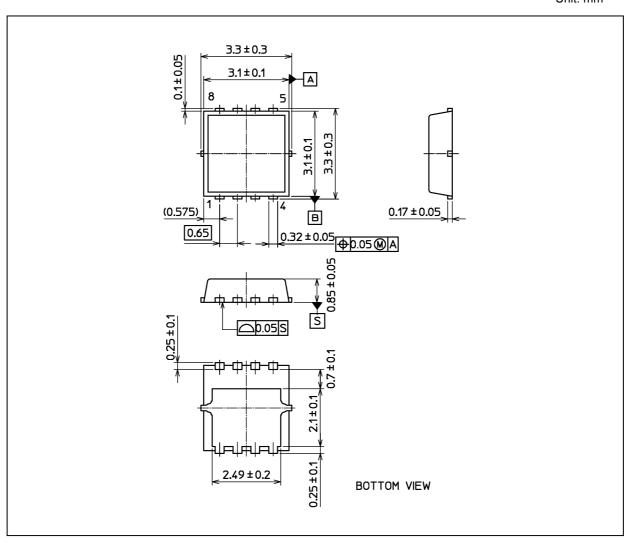


Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



Package Dimensions

Unit: mm



Weight: 0.026 g (typ.)

| Package Name(s) | |
|------------------------|--|
| TOSHIBA: 2-3X1S | |
| Nickname: TSON Advance | |



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